



**GHXS045A120S-D3**

VDC	1200 V
I <sub>F</sub>	45 A
T <sub>j,max</sub>	175 °C

## 1200V SiC Power Module Dual Diode Pack

### Features

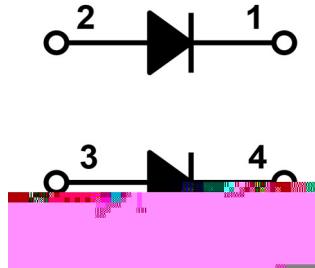
- SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on V<sub>F</sub>
- Low stray inductance
- High junction temperature operation
- All parts tested to greater than 1,400V

### Benefits

- Outstanding performance at high frequency operation
- Low loss and low EMI noise
- Very rugged and easy mounting
- Internally isolated package (AlN)
- Low junction to case thermal resistance
- Easy paralleling due to positive T<sub>C</sub> of V<sub>F</sub>
- RoHS compliant

### Applications

- Switched-mode power supply
- Induction heater
- Welding equipment
- Charging station



Parallel

### Package

Part #	Package	Marking
GHXS045A120S-D3	SOT-227	GHXS045A120S-D3



**Maximum Ratings**, at T<sub>j</sub>=25 °C, unless otherwise specified (per leg)

Characteristics	Symbol	Conditions	Values	Unit
Continuous forward current	I <sub>F*</sub>	T <sub>C</sub> =25 °C, T <sub>j</sub> =175 °C	116	A
		T <sub>C</sub> =146 °C, T <sub>j</sub> =175 °C	45	
		T <sub>C</sub> =150 °C, T <sub>j</sub> =175 °C	40	
Surge non-repetitive forward current sine halfwave	I <sub>FSM</sub>	T <sub>C</sub> =25 °C, t <sub>p</sub> =8.3 ms	340	A
		T <sub>C</sub> =110 °C, t <sub>p</sub> =8.3 ms	310	
Non-repetitive peak forward current	I <sub>F,max</sub>	T <sub>C</sub> =25 °C, t <sub>p</sub> =10 µs	1700	A
<sup>2</sup> value	J <sup>2</sup>	T <sub>C</sub> =25 °C, t <sub>p</sub> =8.3 ms	480	A <sup>2</sup> s
		T <sub>C</sub> =110 °C, t <sub>p</sub> =8.3 ms	398	
Repetitive peak reverse voltage	V <sub>RRM</sub>	T <sub>j</sub> =25 °C	1200	V
Diode ruggedness		Turn-on slew rate, repetitive	200	V/ns
Power dissipation	P <sub>tot*</sub>	T <sub>C</sub> =25 °C	484	W
Operating junction temperature	T <sub>j</sub>		-55...175	°C
Storage temperature	T <sub>storage</sub>		-55...150	°C

Notes: \*Typical R<sub>thJC</sub> used

Failure Per

- ..... -55C
- 25C
- - - 75C
- - - 125C
- 175C

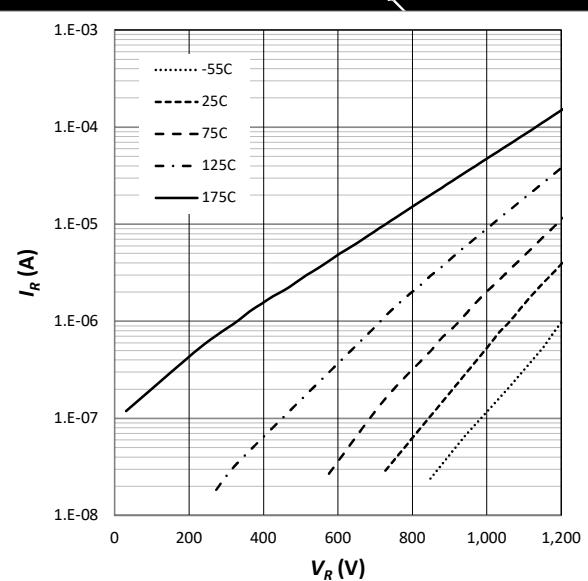


Fig. 1

Reverse Characteristics (p)

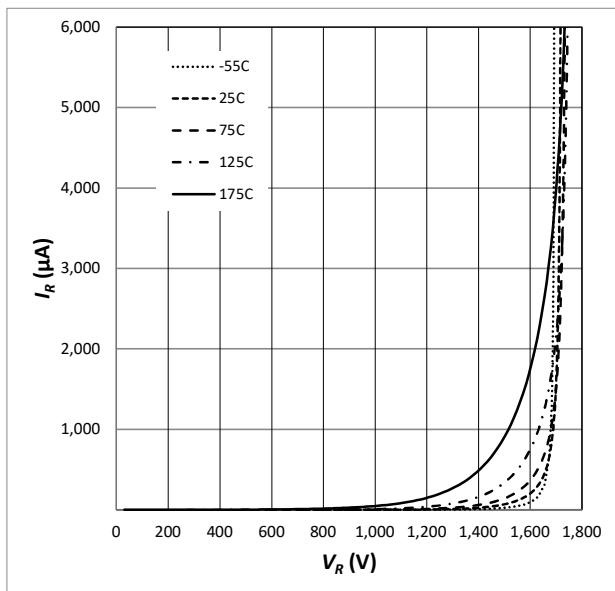
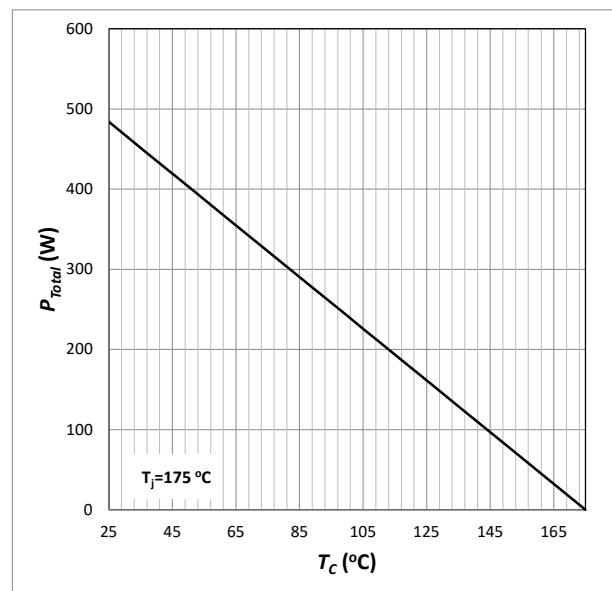
Fig. 3 Reverse Characteristics (parameterized on  $T_j$ )

Fig. 4 Power Derating

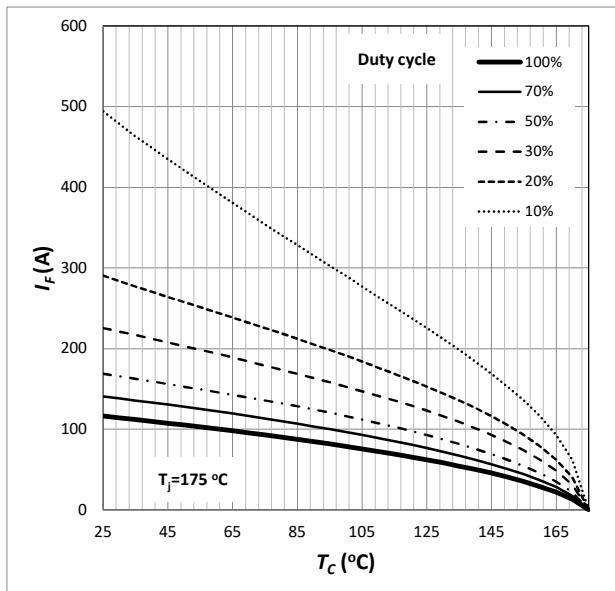


Fig. 5 Current Derating

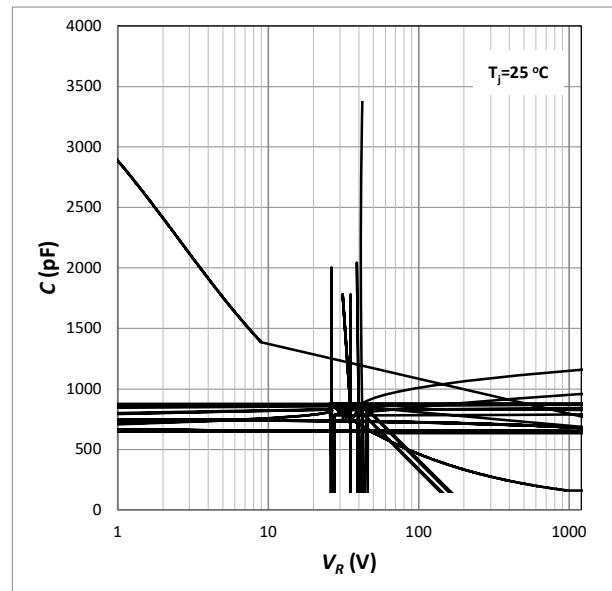
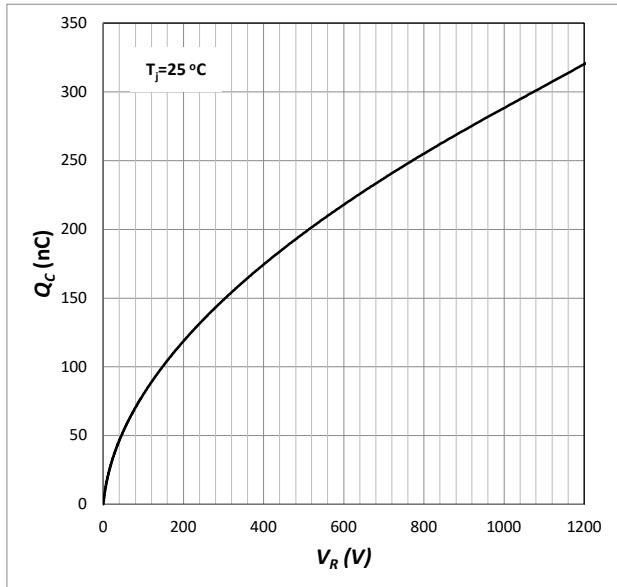


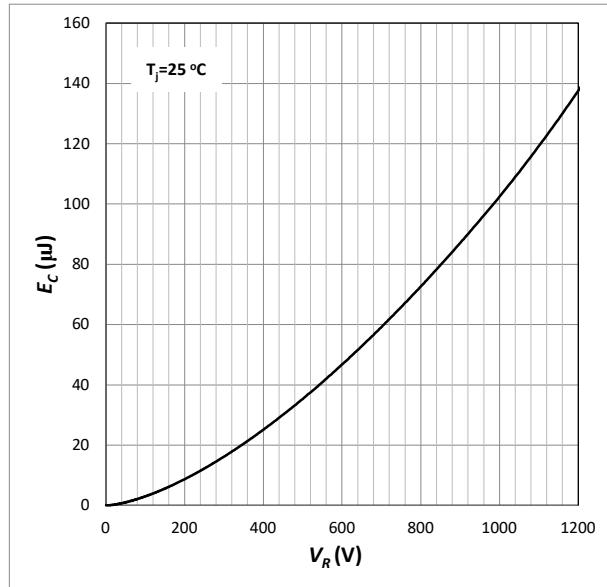
Fig. 6 Capacitance

# 1200V SiC Power Module

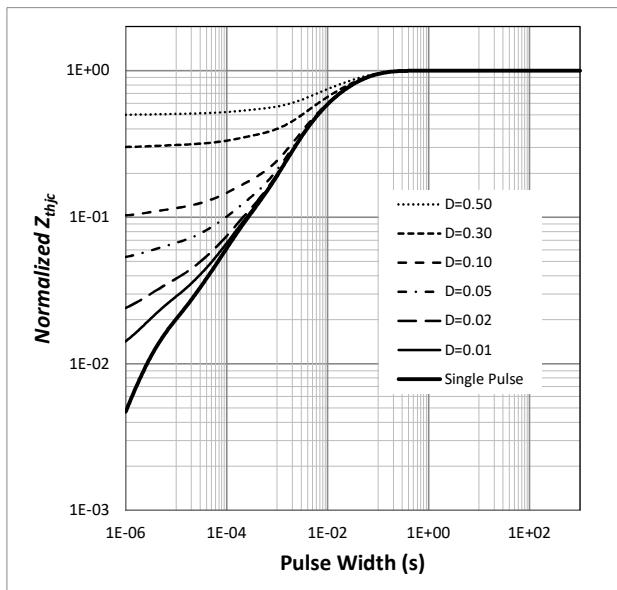
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**Fig. 7 Capacitive Charge**



**Fig. 8 Typical Capacitance Stored Energy**

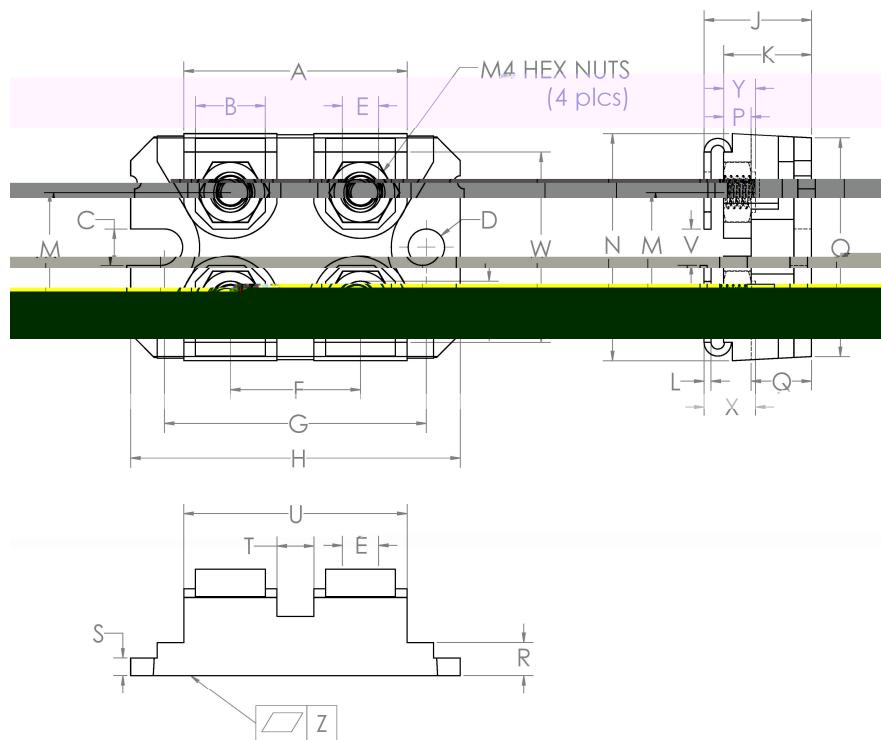


**Fig. 9 Transient Thermal Impedance**

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## Package Dimensions SOT-227



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	31.67	31.90	1.247	1.256
B	7.95	8.18	0.313	0.322
C	4.14	4.24	0.163	0.167
D	4.14	4.24	0.163	0.167
E	4.14	4.24	0.163	0.167
F	14.94	15.09	0.588	0.594
G	30.15	30.25	1.187	1.191
H	38.00	38.10	1.496	1.500
I	4.75	4.83	0.187	0.190
J	11.68	12.19	0.460	0.480
K	9.45	9.60	0.372	0.378
L	0.76	0.84	0.030	0.033
M	12.62	12.88	0.497	0.507
N	25.15	25.30	0.990	0.996
O	24.79	25.04	0.976	0.986
P	3.02	3.15	0.119	0.124
Q	6.71	6.96	0.264	0.274
R	4.17	4.42	0.164	0.174
S	2.08	2.13	0.082	0.084
T	3.28	3.63	0.129	0.143
U	26.75	26.90	1.053	1.059
V	3.86	4.24	0.152	0.167
W	20.55	26.90	0.809	0.814
X	5.45	5.85	0.215	0.230
Y	3.15	3.66	0.124	0.144
Z	0.00	0.13	0.000	0.005

## Revision History

Date	Revision	Notes
9/6/2013	1.0	Initial release
6/4/2014	1.1	Add the part number, pin assignment table.
1/3/2020	1.2	Applied company name change.
11/12/2020	1.3	Updated parameters.

## Notes

### RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of [www.SemiQ.com](http://www.SemiQ.com).

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